AGM-024

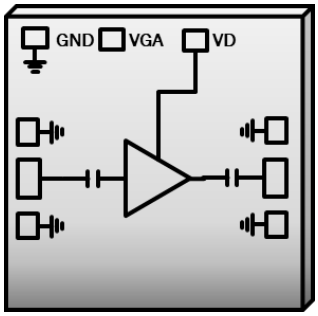
GaAs pHEMT MMIC
2.0 – 4.0GHz Low Noise Amplifier

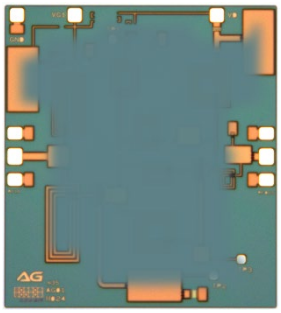
Typical Applications

- Test Instrumentation
- Military EW Systems
- Fiber Optics
- Telecom Infrastructure
- 5G Base Stations

- Frequency Range: 2.0 – 4.0 GHz
- Noise Figure: 0.65dB
- Gain: 27.5dB
- P1dB: + 12.5dBm
- Self-Biased: +7V @ 30mA Single Supply
- 50Ω Matched Input/Output DC blocked
- Chip Size: 1.8 x 2.0 x 0.1 mm^2

Features





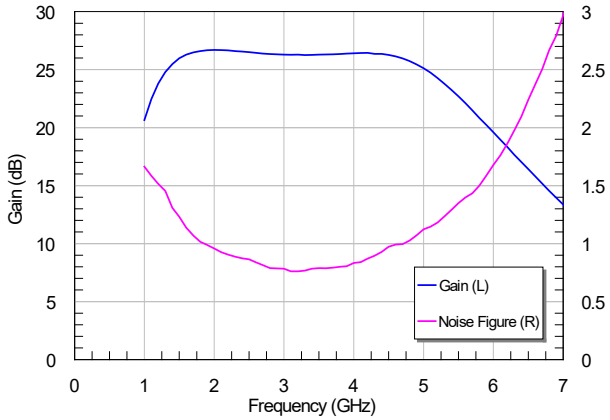
Electrical Specifications (TA = +25°C, VDD = +7V, IDD = 30mA)

Parameter	Units	Minimum	Typical	Maximum
Frequency	GHz	2.0		4.0
Gain	dB	27.4	27.5	27.8
Gain Flatness	dB		± 0.2	
Noise Figure	dB		0.65	0.7
Input Return Loss	dB	12		
Output Return Loss	dB	13.5	16	
P1dB	dBm		12.5	
Psat	dBm		14.0	
Supply Voltage	V		+7	
Supply Current	mA		30	
DC Dissipated Power	mW		210	
Package Type			Die	

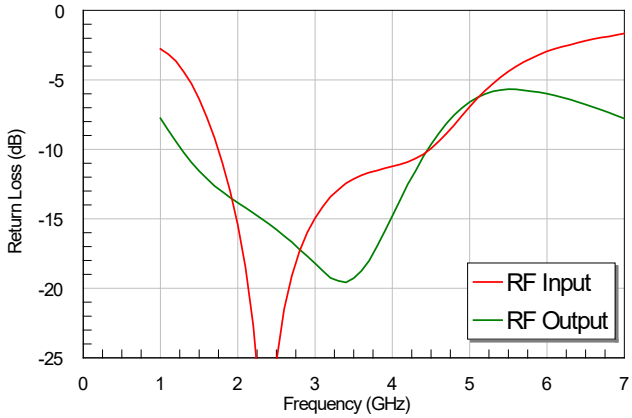
Low Noise Amplifiers - Die

Performance Graphs (5V 25mA 25°C)

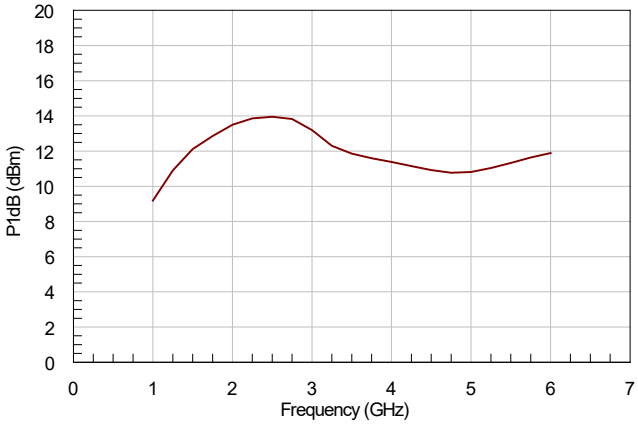
Gain and Noise Figure



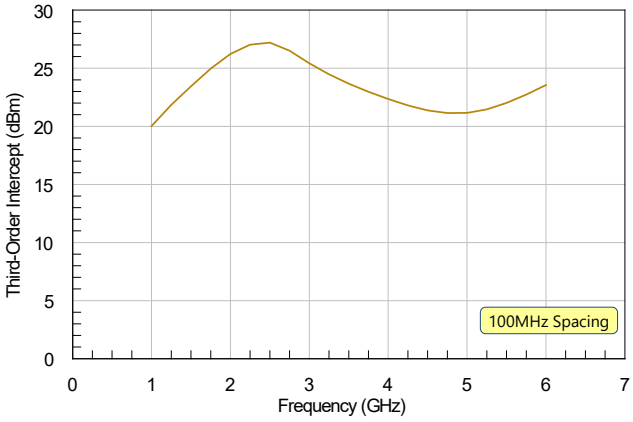
Return Losses



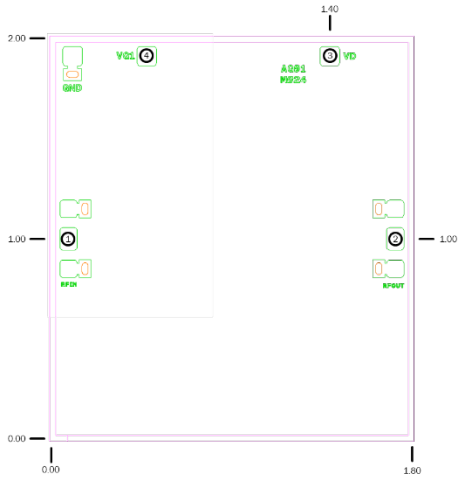
Output Power P1dB (Simulated)



TOI (Simulated)



Outline Drawing (dimensions in mm)



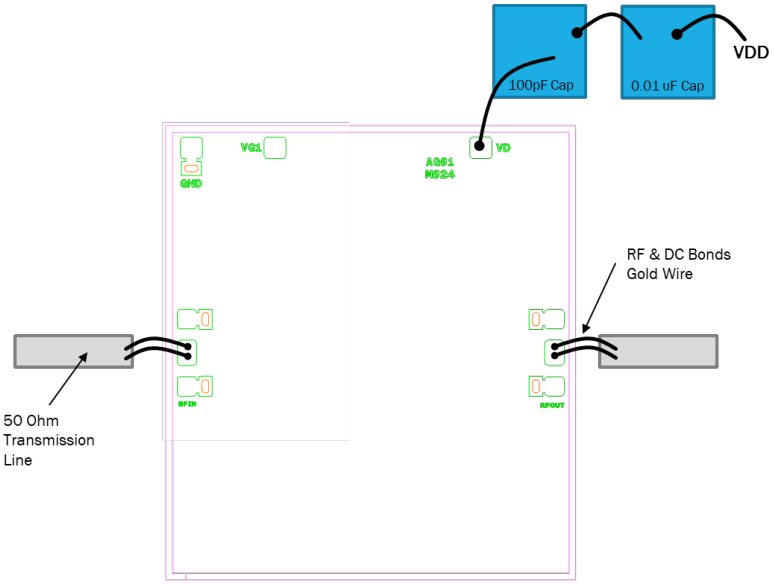
Pad Descriptions

Pad	Function	Pad Size	Description
1	RFIN	75x100µm	AC coupled 50Ω Matched
2	RFOUT	75x100µm	AC coupled 50Ω Matched
3	VDD	85x85µm	Drain Power Supply voltage, bypass capacitors needed
4	AGC	85x85µm	No connect needed – if AGC function needed vary 0-5V
Die Bottom	GND	Backside	Epoxy/Solder to Baseplate

Absolute Maximum Ratings

Drain Bias Voltage (VDD)	+9V DC
RF Input Power (RFIN)	+20dBm*
Channel Temperature	150°C
Storage Temperature	-65 to 150°C
Operating Temperature	-55 to 85°C

Assembly Diagram



Assembly Notes:

1. Die Thickness is 100µm
2. Backside and Bondpad metallization: 4µm gold
3. Silver Epoxy or AuSn Eutectic attach MMIC

Die Packaging Information

- GP-8 (Gel-Pak)